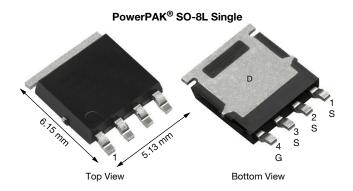
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Vishay Siliconix

# Automotive P-Channel 80 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	-80				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = -10 V	0.025				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -6 \text{ V}$	0.029				
I <sub>D</sub> (A)	-32				
Configuration	Single				

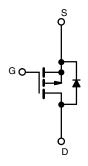
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



P-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK® SO-8L
Lead (Pb)-free and halogen-free	SQJ469EP (for detailed order number please see <a href="https://www.vishay.com/doc?79776">www.vishay.com/doc?79776</a> )

ABSOLUTE MAXIMUM RATINGS (	$T_C = 25  ^{\circ}C$ , unles	s otherwise noted	)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	-80	V
Gate-source voltage		$V_{GS}$	± 20	V
Continuous drain current <sup>a</sup>	T <sub>C</sub> = 25 °C	1	-32	
Continuous drain current "	T <sub>C</sub> = 125 °C	I <sub>D</sub>	-24	
Continuous source current (diode conduction) a		I <sub>S</sub>	-32	Α
Pulsed drain current b		I <sub>DM</sub>	-128	
Single pulse avalanche current  L = 0.1 mH		I <sub>AS</sub>	-45	
Single pulse avalanche energy	e energy L = 0.1 mH		101	mJ
Maximum power dissipation	T <sub>C</sub> = 25 °C	D	100	W
aximum power dissipation	T <sub>C</sub> = 125 °C	$P_{D}$	33	VV
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering recommendations (peak temperature) d, e			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	$R_{thJA}$	65	°C/W
Junction-to-case (drain)		$R_{thJC}$	1.5	C/VV

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq 300 \,\mu\text{s}$ , duty cycle  $\leq 2 \,\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (<a href="https://www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = -250 μA	-80	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.5	-2.0	-2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	$V_{DS} = -80 \text{ V}$	-	-	-1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -80 V, T <sub>J</sub> = 125 °C	-	-	-50	μΑ
-		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -80 V, T <sub>J</sub> = 175 °C	-	-	-150	1
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	V <sub>DS</sub> = -5 V	-30	-	-	Α
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10.2 A	-	0.021	0.025	
Dunin Course On Chata Basistana 3		V <sub>GS</sub> = -10 V	T <sub>J</sub> = 125 °C	-	0.036	0.043	
Drain-Source On-State Resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	T <sub>J</sub> = 175 °C	-	0.045	0.054	Ω
		V <sub>GS</sub> = -6 V	I <sub>D</sub> = -8.1 A	1	0.024	0.029	
Forward Transconductance b	9fs	$V_{DS} = -15 \text{ V}, I_{D} = -10.2 \text{ A}$		-	35	_	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	4250	5100	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V, f} = 1 \text{ MHz}$	-	250	300	рF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	215	260	1
Total Gate Charge c	$Q_g$			-	101	155	
Gate-Source Charge c	Q <sub>gs</sub>	V <sub>GS</sub> = -10 V	$V_{DS} = -40 \text{ V}, I_{D} = -10.2 \text{ A}$	-	13	-	nC
Gate-Drain Charge c	$Q_{gd}$			-	21	-	1
Gate Resistance	R <sub>g</sub>		f = 1 MHz	1.8	3.2	4.6	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	16	20	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -40 \text{ V}, \text{ R}_{L} = 4.9 \Omega$ $I_{D} \cong -8.1 \text{ A}, \text{ V}_{GEN} = -10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	16	20	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	150	180	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	40	50	
Source-Drain Diode Ratings and Chara	acteristics b						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	-128	Α
		I <sub>F</sub> = -8.1 A, V <sub>GS</sub> = 0					

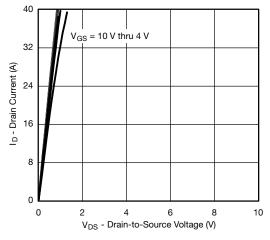
### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

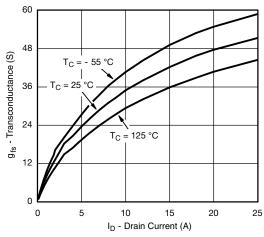
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



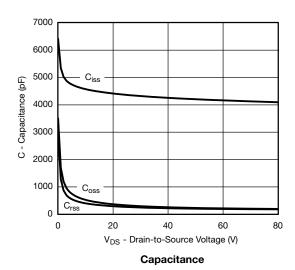
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

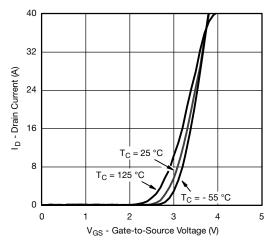


### **Output Characteristics**

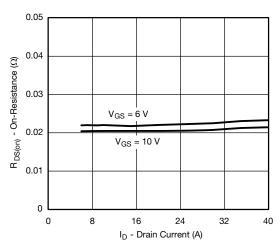


Transconductance

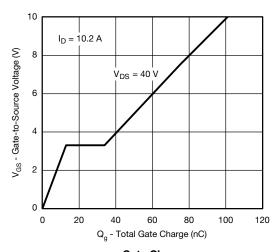




**Transfer Characteristics** 



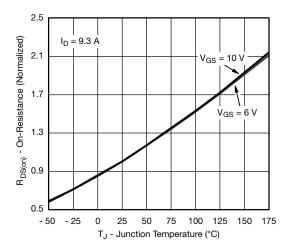
On-Resistance vs. Drain Current



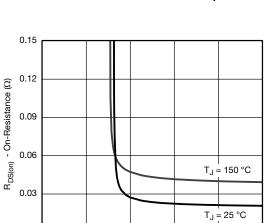
Gate Charge



## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature

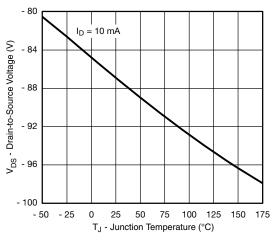


 $\label{eq:VGS} V_{GS} \text{ - Gate-to-Source Voltage (V)}$  On-Resistance vs. Gate-to-Source Voltage

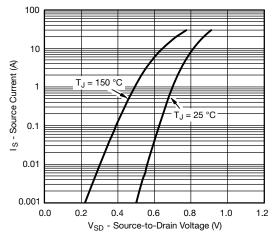
6

10

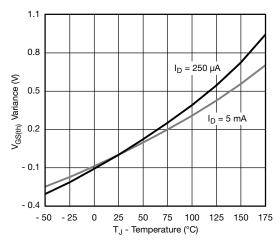
8



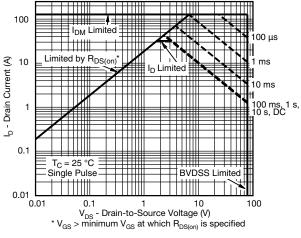
**Drain-Source Breakdown vs. Junction Temperature** 



**Source Drain Diode Forward Voltage** 



Threshold Voltage

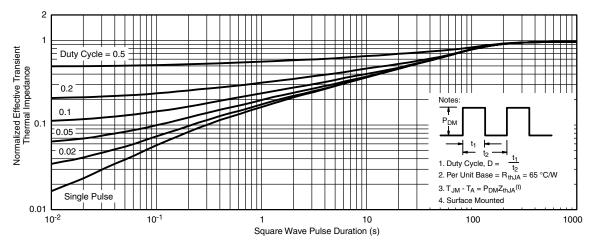


Safe Operating Area

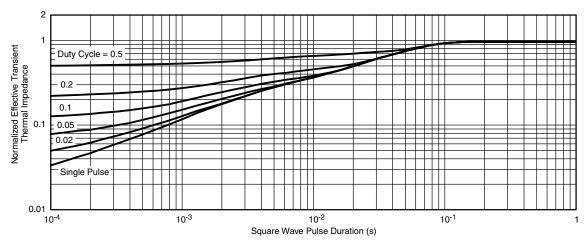
0.00 **L** 



## **THERMAL RATINGS** (T<sub>C</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

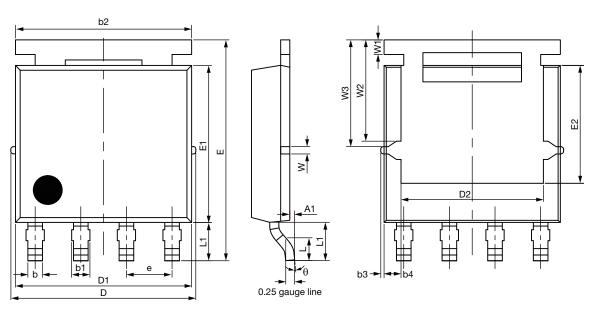
#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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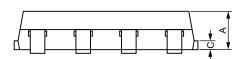


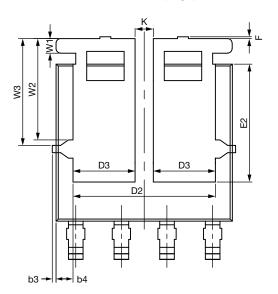
# PowerPAK® SO-8L Case Outline 1



Topside view

Backside view (single)





Backside view (dual)



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DIM	MILLIMETERS				INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC		0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	3.18	3.28	3.38	0.125	0.129	0.133		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
K		0.51			0.020			
W		0.23			0.009			
W1	0.41			0.016				
W2		2.82			0.111			
W3		2.96			0.117			
θ	0°	-	10°	0°	-	10°		

ECN: S19-0643-Rev. E, 05-Aug-2019

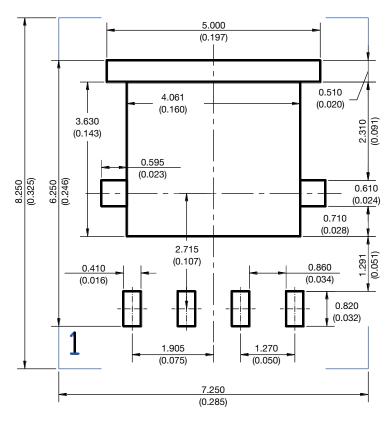
DWG: 5976

#### Note

• Millimeters will gover



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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